



N-Channel Enhancement-Mode MOSFET Transistors

PRODUCT SUMMARY				
Part Number	$V_{(BR)DSS}$ Min (V)	$r_{DS(on)}$ Max (Ω)	$V_{GS(th)}$ (V)	I_D (A)
TN0601L	60	1.8 @ $V_{GS} = 10$ V	0.5 to 2	0.47
VN0606L		3 @ $V_{GS} = 10$ V	0.8 to 2	0.33
VN66AFD		3 @ $V_{GS} = 10$ V	0.8 to 2.5	1.46

FEATURES

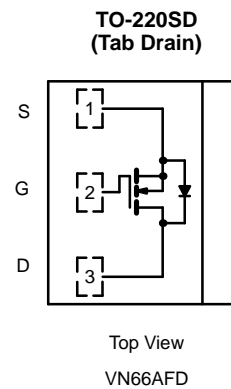
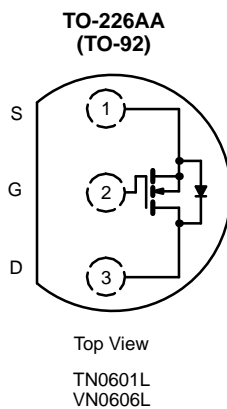
- Low On-Resistance: 1.2 Ω
- Low Threshold: <1.6 V
- Low Input Capacitance: 35 pF
- Fast Switching Speed: 9 ns
- Low Input and Output Leakage

BENEFITS

- Low Offset Voltage
- Low-Voltage Operation
- Easily Driven Without Buffer
- High-Speed Circuits
- Low Error Voltage

APPLICATIONS

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	TN0601L	VN0606L	VN66AFD ^b	Unit
Drain-Source Voltage	V_{DS}	60	60	60	V
Gate-Source Voltage	V_{GS}	± 20	± 30	± 30	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	$T_A = 25^\circ\text{C}$	I_D	0.47	0.33	A
	$T_A = 100^\circ\text{C}$		0.29	0.21	
Pulsed Drain Current ^a		I_{DM}	1.5	1.6	3
Power Dissipation	$T_A = 25^\circ\text{C}$	P_D	0.8	0.8	W
	$T_A = 100^\circ\text{C}$		0.32	0.32	
Maximum Junction-to-Ambient		R_{thJA}	156	156	$^\circ\text{C/W}$
Maximum Junction-to-Case		R_{thJC}		8.3	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		$^\circ\text{C}$

Notes

- a. Pulse width limited by maximum junction temperature.
b. Reference case for all temperature testing.



SPECIFICATIONS (T _A = 25 °C UNLESS OTHERWISE NOTED)										
Parameter	Symbol	Test Conditions	Typ ^a	Limits						Unit
				TN0601L		VN0606L		VN66AFD		
				Min	Max	Min	Max	Min	Max	
Static										
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 10 μA	70	60		60		60		V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 0.25 mA	1.6	0.5	2					V
		V _{DS} = V _{GS} , I _D = 1 mA	1.7			0.8	2	0.8	2.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±30 V					±100		±100	nA
		T _C = 125 °C							±500	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±10					μA
		V _{DS} = 60 V, V _{GS} = 0 V					10			
		T _J = 125 °C					500			
		V _{DS} = 48 V, V _{GS} = 0 V			1				1	
		T _J = 125 °C			100					
		T _C = 125 °C							10	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 10 V, V _{GS} = 4.5 V	0.5	0.25						A
		V _{DS} = 10 V, V _{GS} = 10 V	2.4	1		1.5		1.5		
Drain-Source On-Resistance ^b	r _{DS(on)}	V _{GS} = 3.5 V, I _D = 0.04 A	4		5					Ω
		V _{GS} = 4.5 V, I _D = 0.25 A	2		3					
		T _J = 125 °C	3.8		6					
		V _{GS} = 5 V, I _D = 0.3 A	2.3					5		
		V _{GS} = 10 V, I _D = 0.5 A	1.2				3			
		T _J = 125 °C	2.3				6			
		V _{GS} = 10 V, I _D = 1 A	1.3		1.8				3	
		T _C = 125 °C	2.5						6	
Forward Transconductance ^b	g _{fs}	V _{DS} = 10 V, I _D = 0.5 A	350	200		170		170		mS
Common Source Output Conductance ^b	g _{os}	V _{DS} = 10 V, I _D = 0.1 A	0.3							
Dynamic										
Input Capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	35		60		50		50	pF
Output Capacitance	C _{oss}		25		50		40		40	
Reverse Transfer Capacitance	C _{rss}		6		10		10		10	
Switching^c										
Turn-On Time	t _{ON}	V _{DD} = 25 V, R _L = 23 Ω I _D ≅ 1 A, V _{GEN} = 10 V R _G = 25 Ω	8		15		10		15	ns
Turn-Off Time	t _{OFF}		9		15		10		15	

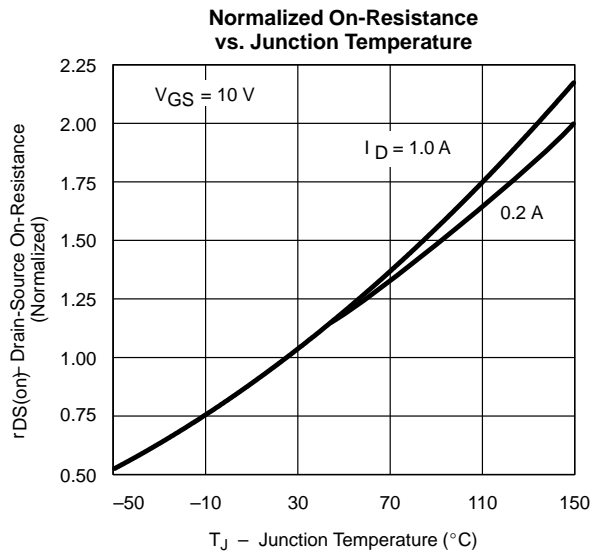
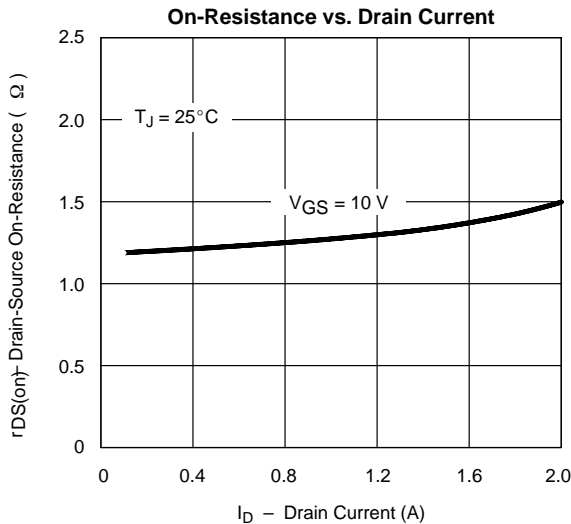
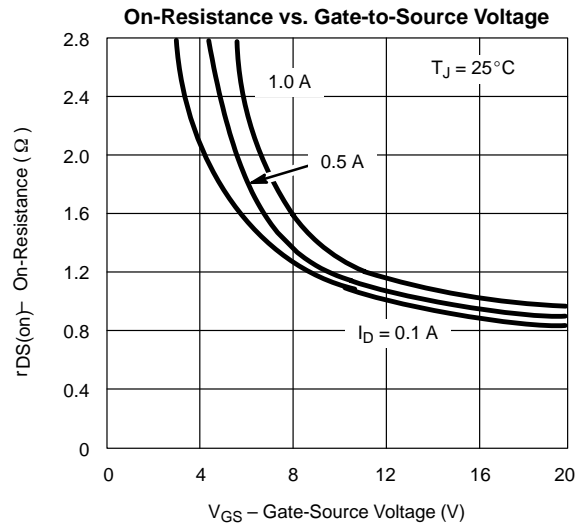
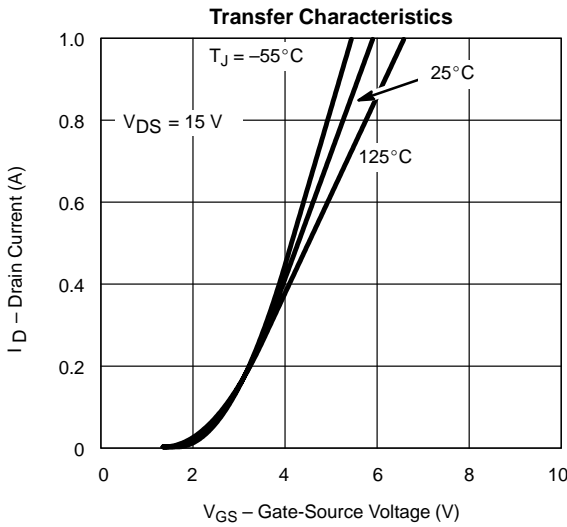
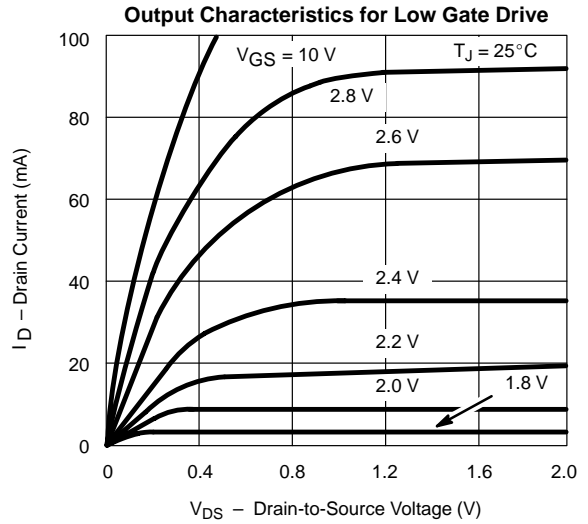
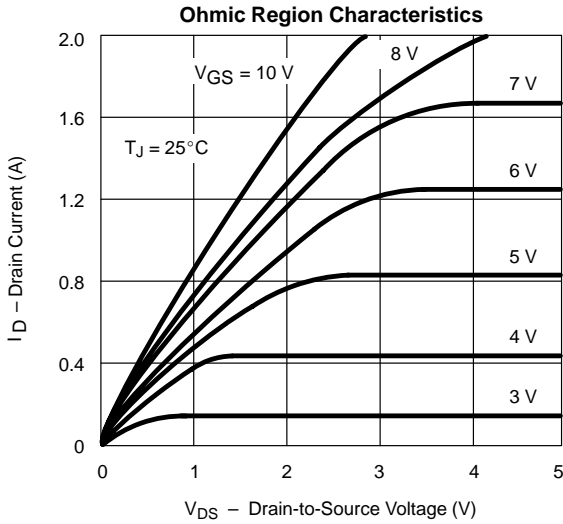
Notes

- a. For DESIGN AID ONLY, not subject to production testing..
- b. Pulse test: PW ≤ 300 μs duty cycle ≤ 2%.
- c. Switching time is essentially independent of operating temperature.

VNDQ06



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



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